

- ★ Green Device
- ★ Super Low Gate
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed

Product Summary

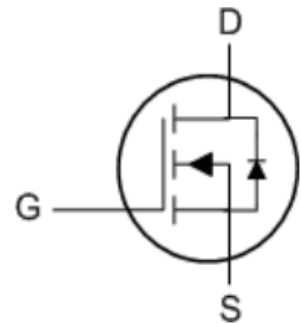
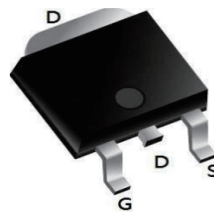
RoHS

BVDSS	RDSON	ID
60V	12mΩ	50A

Description

The 50N06 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and and gate charge for most of the synchronous buck converter applications. The 50N06 meets the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units	
V _{DSS}	Drain-Source Voltage	60	V	
V _{GSS}	Gate-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _C = 25°C	50	A
		T _C = 100°C	33	A
I _{DM}	Pulsed Drain Current <small>note1</small>	200	A	
EAS	Single Pulsed Avalanche Energy <small>note2</small>	68	mJ	
P _D	Power Dissipation	T _C = 25°C	87.7	W
R _{θJC}	Thermal Resistance, Junction to Case	1.6	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_b=250\mu A$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V,$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}= \pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_b=250\mu A$	1	1.6	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_b=30A$	-	12	17	m Ω
		$V_{GS}=4.5V, I_b=20A$	-	16	25	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	2900	-	pF
C_{oss}	Output Capacitance		-	140	-	pF
C_{riss}	Reverse Transfer Capacitance		-	120	-	pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_b=30A, V_{GS}=10V$	-	50	-	nC
Q_{gs}	Gate-Source Charge		-	6	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	15	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30V, I_b=30A, R_g=1.8\Omega, V_{GS}=10V$	-	7.4	-	ns
t_r	Turn-on Rise Time		-	5.1	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	28.2	-	ns
t_f	Turn-off Fall Time		-	5.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=30A, dI/dt=100A/\mu s$	-	28	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	40	-	nC

Notes:

- 1.Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- 2.EAS condition : $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=16A$
- 3.Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Electrical and Thermal Characteristics (Curves)

Figure 1: Output Characteristics

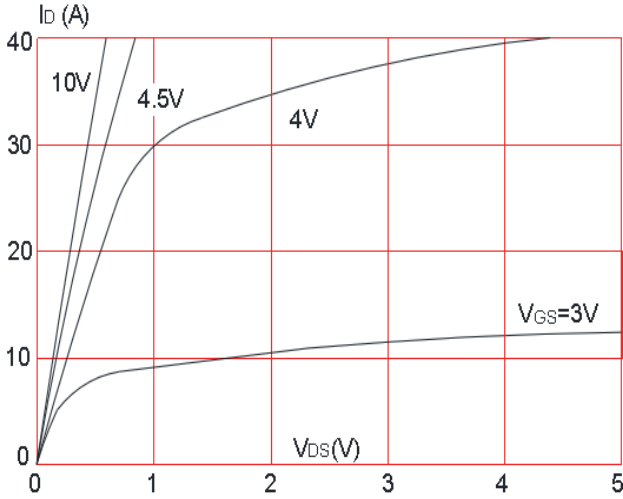


Figure 2: Transfer Characteristics

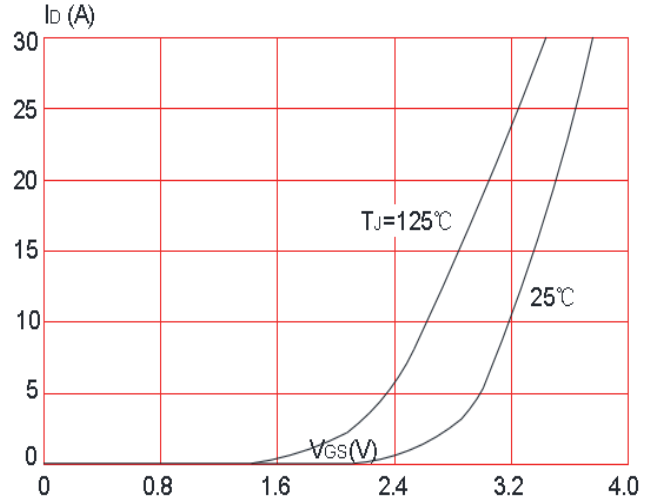


Figure 3: On-resistance vs. Drain Current

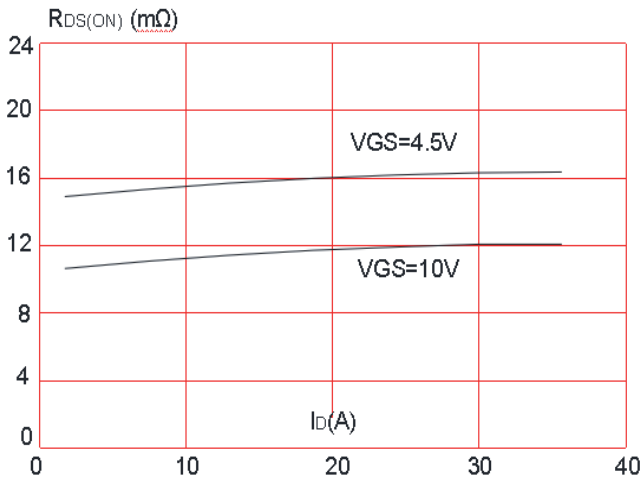


Figure 4: Body Diode Characteristics

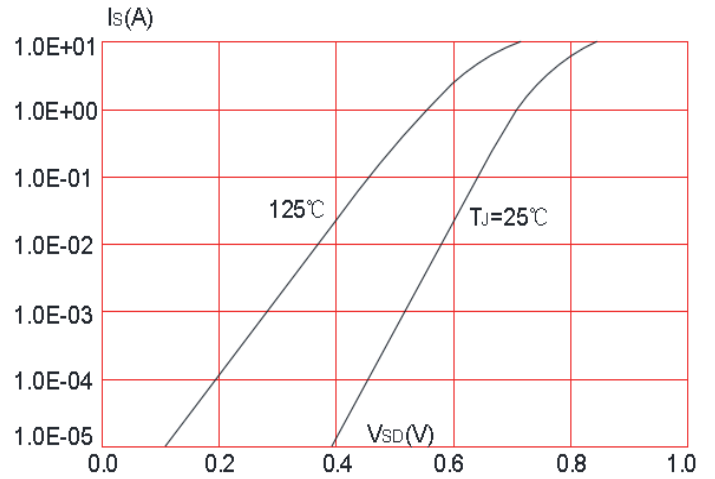


Figure 5: Gate Charge Characteristics

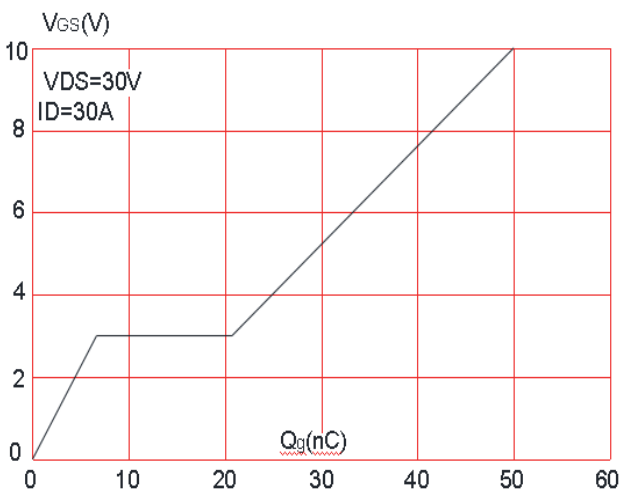
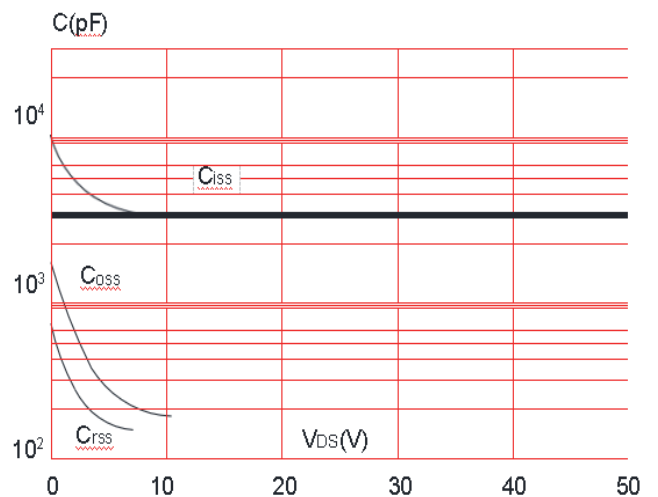


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage

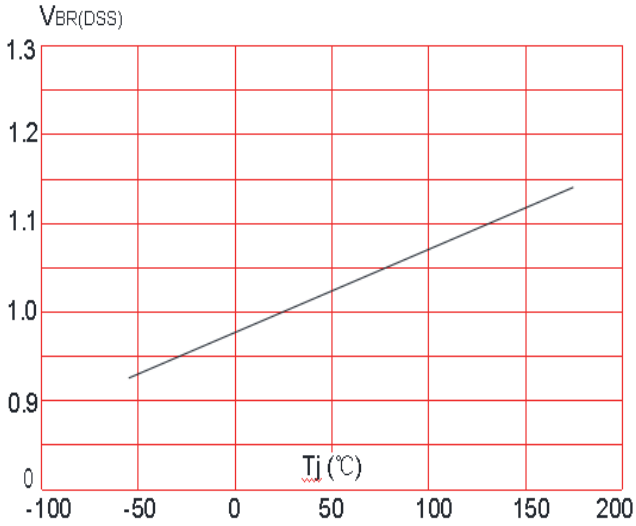


Figure 8: Normalized on Resistance vs. Junction Temperature

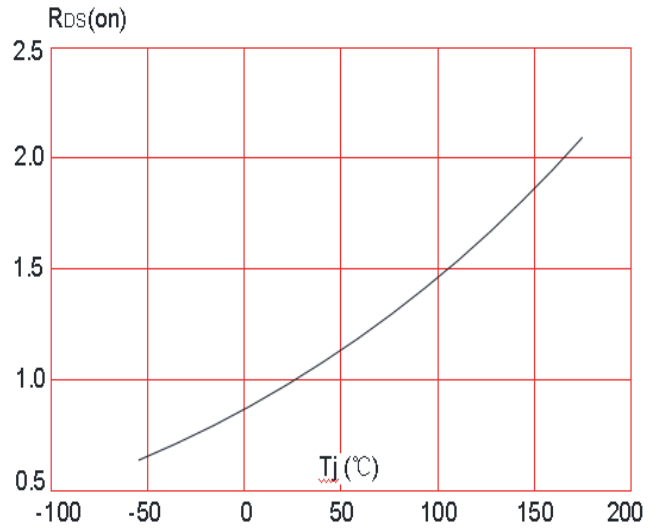


Figure 9: Maximum Safe Operating Area

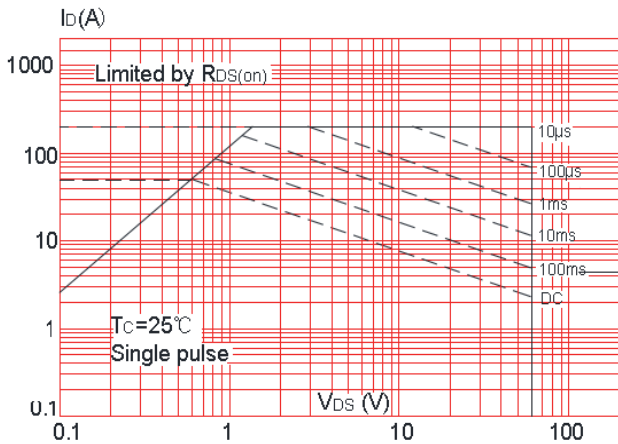


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

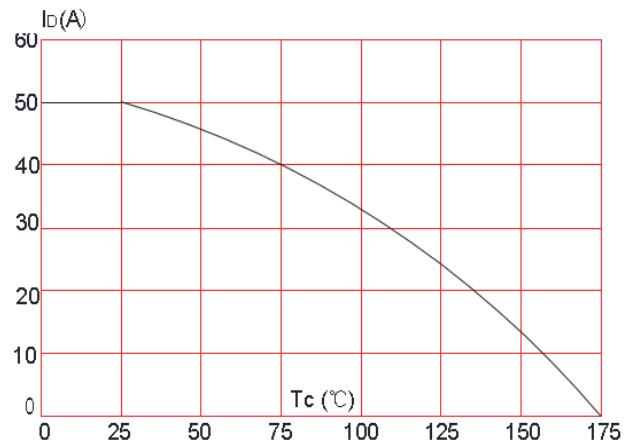
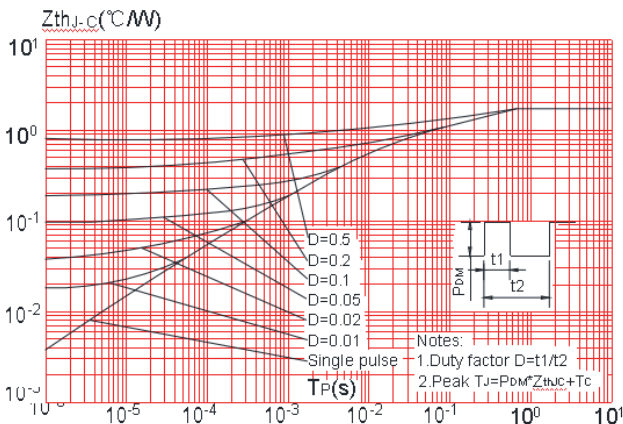
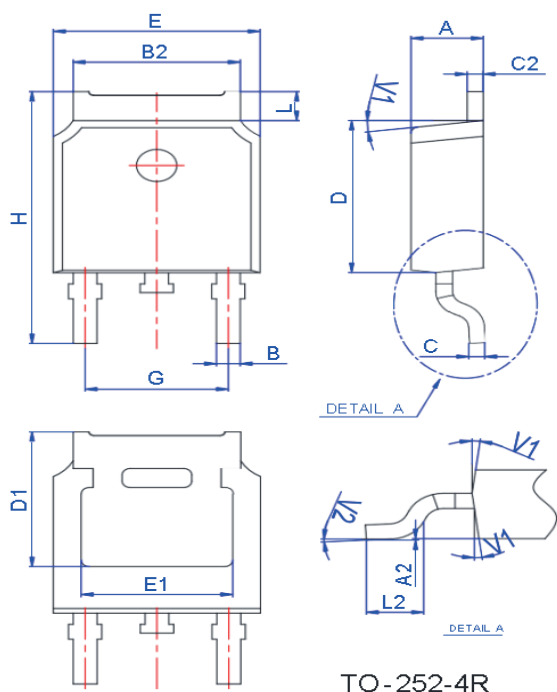


Figure 11: Maximum Effective Transient Thermal Impedance

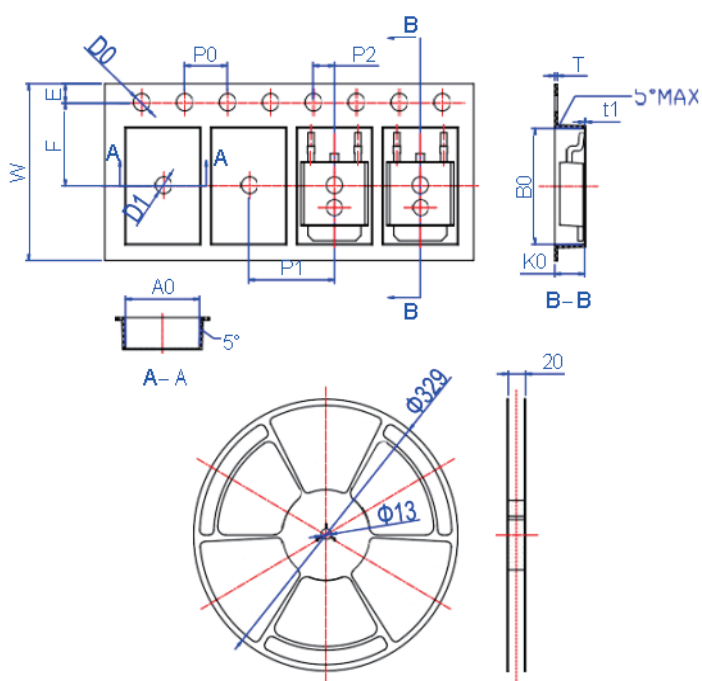


Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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